

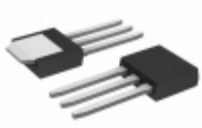


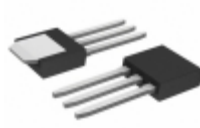
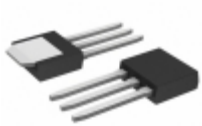



	<b>GP2M005A060CG</b>	
	<b>Hersteller-Teilenummer:</b>	GP2M005A060CG
	<b>Hersteller / Marke:</b>	Global Power Technologies Group
	<b>Teil der Beschreibung:</b>	MOSFET N-CH 600V 4.2A DPAK
<p>Image may be representation. See specs for product details.</p>	<b>Datenblätter:</b>	 <a href="#">GP2M005A060CG.pdf</a>
	<b>RoHs Status:</b>	Bleifrei / RoHS-konform
	<b>Lagerzustand:</b>	New original, 4888 pcs Stock Available.
	<b>Liefern von:</b>	Hong Kong
	<b>Versandweg:</b>	DHL/Fedex/TNT/UPS/EMS

### Spezifikationen

Teilenummer	GP2M005A060CG
Hersteller	Global Power Technologies Group
Beschreibung	MOSFET N-CH 600V 4.2A DPAK
Kategorie	<a href="#">Diskrete Halbleiterprodukte</a> > <a href="#">Transistoren-FETs</a> ,
Teilstatus	4888 pcs Stock
Serie	-
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-252-3, DPak (2 Leads + Tab), SC-63
Supplier Device-Gehäuse	D-Pak
Verlustleistung (max)	98.4W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	600V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	4.2A (Tc)
Rds On (Max) @ Id, Vgs	2.1 Ohm @ 2.1A, 10V
VGS (th) (Max) @ Id	5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	14nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	658pF @ 25V
Verpackung	Tape & Reel (TR)

GP2M005A060CG ist neu im Original. Suche GP2M005A060CG Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie GP2M005A060CG Global Power Technologies Group mit Garantie und Vertrauen. Anfrage GP2M005A060CG: [Info@Y-IC.com](mailto:Info@Y-IC.com)

Sie können auch interessiert sein:

 <p><b>GP2M005A060PG</b> Global Power Technologies Group MOSFET N-CH 600V 4.2A IPAK</p>	 <p><b>GP2M005A050HG</b> Global Power Technologies Group MOSFET N-CH 500V 4.5A TO220</p>	 <p><b>GP2M007A065HG</b> Global Power Technologies Group MOSFET N-CH 650V 6.5A TO220</p>	 <p><b>GP2M004A065PG</b> Global Power Technologies Group MOSFET N-CH 650V 4A IPAK</p>
 <p><b>GP2M005A050PG</b> Global Power Technologies Group MOSFET N-CH 500V 4.5A IPAK</p>	 <p><b>GP2M005A050CG</b> Global Power Technologies Group MOSFET N-CH 500V 4.5A DPAK</p>	 <p><b>GP2M005A060FG</b> Global Power Technologies Group MOSFET N-CH 600V 4.2A TO220F</p>	 <p><b>GP2M005A050FG</b> Global Power Technologies Group MOSFET N-CH 500V 4.5A TO220F</p>

### heiße Teile

Mehr

GP200E1M-G1	GP200E1MTR-G1	GP200EMTR-G1	GP200MTR-G1	GP2A231LRSA
GP2A25J0000F	GP2A25J0000F	GP2A25NJ	GP2A28A1J00F	GP2A28N1J00F
GP2AP002A00F	GP2AP002S00F	GP2AP003A10F	GP2AP007A00F	GP2AP008T00F
GP2AP030A00F	GP2AP052A00F	GP2AP052A00F	GP2L26K2	GP2M002A060FG
GP2M004A060PG	GP2M004A065FG	GP2M004A065PG	GP2M005A050PG	GP2M005A060FG
GP2M005A060PGH	GP2M008A060FGH	GP2M010A060F	GP2M010A065F	GP2M011A090NG
GP2M012A080NG	GP2M020A050H	GP2M020A060N	GP2S24J0000F	GP2S27T3
GP2S27T3J00F	GP2S27V6	GP2S29SVJ00F	GP2S40JJ000F	GP2S700HCP
GP2S700HCP	GP2W0004YP	GP2W0110YPS	GP2W0112YPOF	GP2W0118YPS
GP2W0150YP0F	GP2W3104XP0F	GP2W3104YP0F	GP2W3106YP0F	GP2W3152YP0F

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